COMPLEMENTARY PAIR SMALL SIGNAL TRANSISTOR IN SOT363

Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of Automotive Applications.

Features

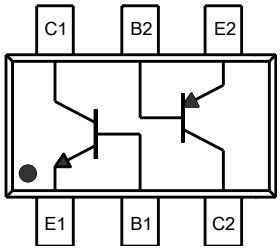
- Two Internally Isolated NPN/PNP Transistors in One Package
- Ideal for Medium Power Amplification and Switching
- Ultra-small Surface Mount Package
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The BC847PNQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.**
  https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: SOT363
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Finish. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.006 grams (Approximate)

SOT363

Top View



Device Schematic
Top View

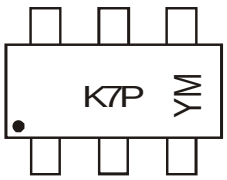
Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
BC847PNQ-7-F	Automotive	K7P	7	8	3,000
BC847PNQ-7R-F	Automotive	K7P	7	8	3,000

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

SOT363



K7P = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: J = 2022)
M = Month (ex: 9 = September)

Date Code Key

Year	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	I	J	K	L	M	N	O	P	R	S

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Absolute Maximum Ratings: NPN, BC847B Type (Q_1) (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	45	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	100	mA
Peak Collector Current	I_{CM}	200	mA
Peak Emitter Current	I_{EM}	200	mA

Absolute Maximum Ratings: PNP, BC857B Type (Q_2) (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-45	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector Current	I_C	-100	mA
Peak Collector Current	I_{CM}	-200	mA
Peak Emitter Current	I_{EM}	-200	mA

Thermal Characteristics – Total Device (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6) Total Device	P_D	200	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	625	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +150	°C

Note: 5. For a device mounted on minimum recommended pad layout with 1oz copper that is on a single-sided 1.6mm FR-4 PCB; the device is measured under still air conditions whilst operating in a steady-state.

Thermal Characteristics – Total Device

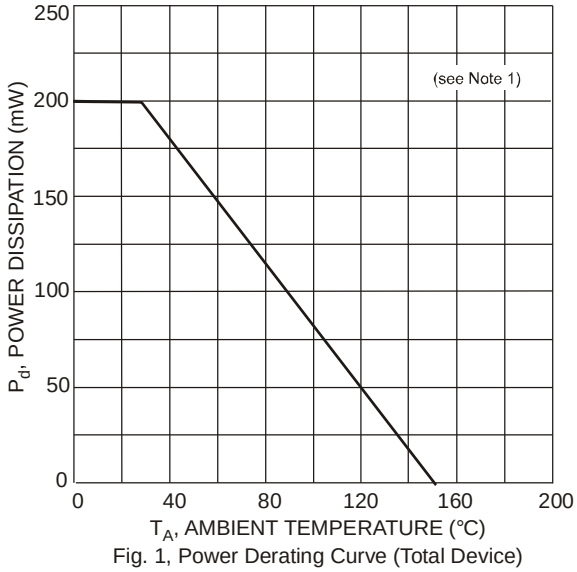


Fig. 1, Power Derating Curve (Total Device)

Electrical Characteristics: NPN, BC847B Type (Q_1) (@T_A = +25°C, unless otherwise specified.)

Characteristic (Note 6)	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	50	—	—	V	I_C = 100µA
Collector-Emitter Breakdown Voltage	BV_{CEO}	45	—	—	V	I_C = 10mA
Emitter-Base Breakdown Voltage	BV_{EBO}	6	—	—	V	I_E = 100µA
DC Current Gain	h_{FE}	200	290	450	—	V_{CE} = 5V, I_C = 2mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	90 200	250 600	mV	I_C = 10mA, I_B = 0.5mA I_C = 100mA, I_B = 5mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	—	700 900	—	mV	I_C = 10mA, I_B = 0.5mA I_C = 100mA, I_B = 5mA
Base-Emitter Voltage	$V_{BE(on)}$	580 —	660 —	700 770	mV	V_{CE} = 5V, I_C = 2mA V_{CE} = 5V, I_C = 10mA
Collector-Cutoff Current	I_{CBO}	— —	— —	15 5	nA µA	V_{CB} = 30V V_{CB} = 30V, T_A = +150°C
Gain Bandwidth Product	f_T	100	300	—	MHz	V_{CE} = 5V, I_C = 10mA, f = 100MHz
Collector-Base Capacitance	C_{cbo}	—	3.5	6	pF	V_{CB} = 10V, f = 1MHz
Noise Figure	NF	—	2	10	dB	V_{CE} = 5V, I_C = 200µA, R_g = 2kΩ, f = 1kHz, Δf = 200Hz

Note: 6. Short duration pulse test used to minimize self-heating effect.

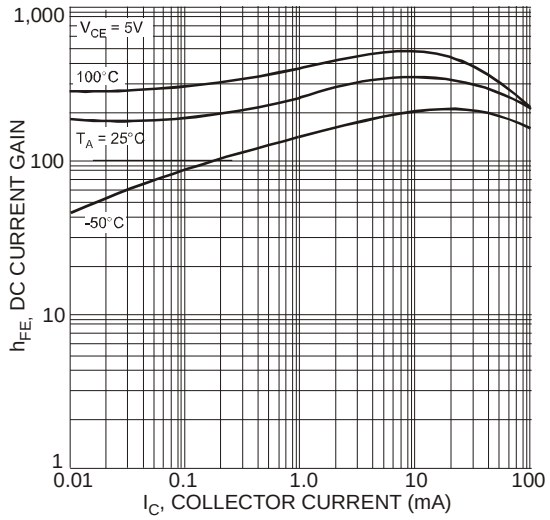


Figure 2. Typical DC Current Gain vs. Collector Current (BC847B Type)

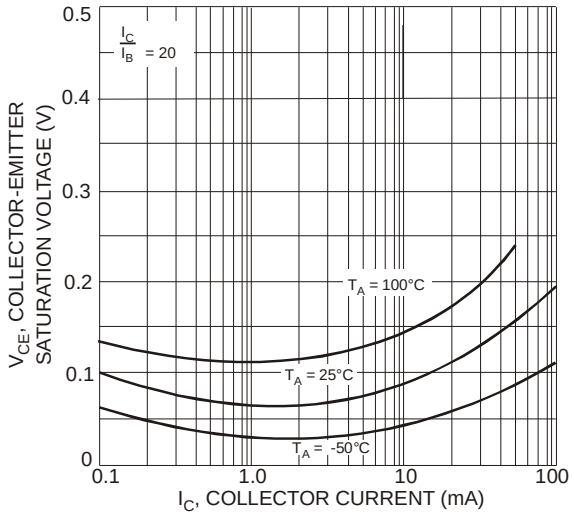


Figure 3. Typical Collector-Emitter Saturation Voltage vs. Collector Current (BC847B Type)

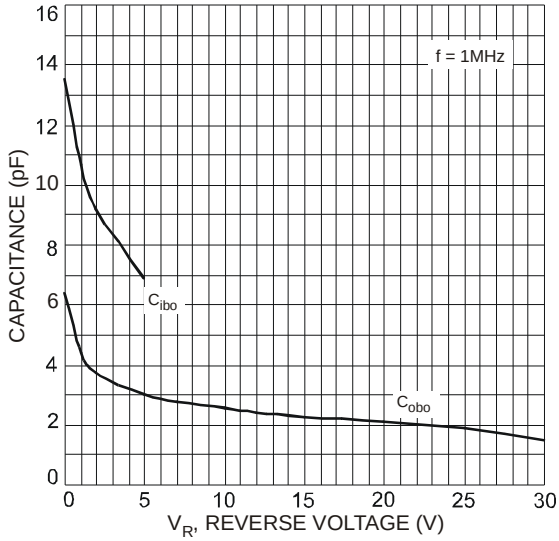


Figure 4. Typical Capacitance Characteristics (BC847B Type)

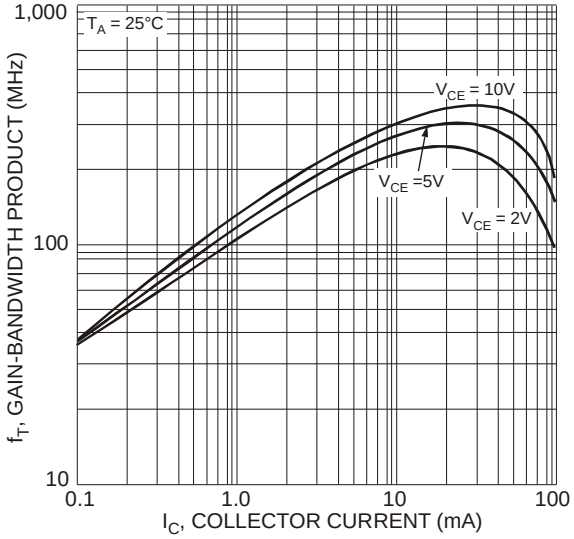


Figure 5. Typical Gain-Bandwidth Product vs. Collector Current (BC847B Type)

Electrical Characteristics: PNP, BC857B Type (Q_2) (@T_A = +25°C unless otherwise specified.)

Characteristic (Note 7)	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	-50	—	—	V	I_C = -100µA
Collector-Emitter Breakdown Voltage	BV_{CEO}	-45	—	—	V	I_C = -10mA
Emitter-Base Breakdown Voltage	BV_{EBO}	-6	—	—	V	I_E = -100µA
DC Current Gain	h_{FE}	220	290	475	—	V_{CE} = -5V, I_C = -2mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	-75 -250	-300 -650	mV	I_C = -10mA, I_B = -0.5mA I_C = -100mA, I_B = -5mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	—	-700 -850	— -950	mV	I_C = -10mA, I_B = -0.5mA I_C = -100mA, I_B = -5mA
Base-Emitter Voltage	$V_{BE(on)}$	-600 —	-650 —	-750 -820	mV	V_{CE} = -5V, I_C = -2mA V_{CE} = -5V, I_C = -10mA
Collector-Cutoff Current	I_{CBO}	— —	— —	-15 -4.0	nA µA	V_{CB} = -30V V_{CB} = -30V, T_A = +150°C
Gain Bandwidth Product	f_T	100	200	—	MHz	V_{CE} = -5V, I_C = -10mA, f = 100MHz
Collector-Base Capacitance	C_{cbo}	—	3	4.5	pF	V_{CB} = -10V, f = 1MHz
Noise Figure	NF	—	—	10	dB	V_{CE} = -5V, I_C = -200µA, R_g = 2kΩ, f = 1kHz, Δf = 200Hz

Note: 7. Short duration pulse test used to minimize self-heating effect.

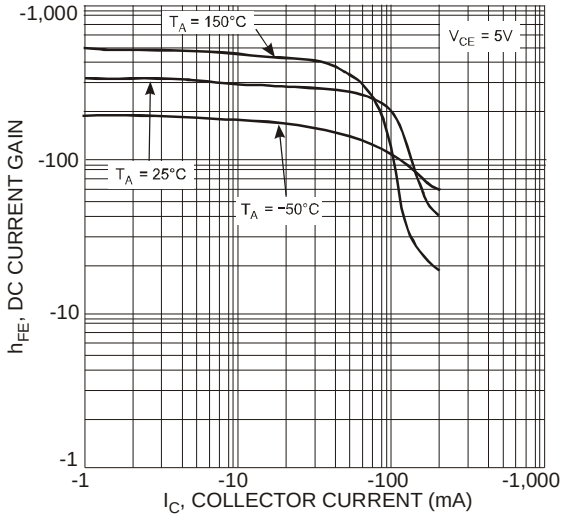


Figure 6. Typical DC Current Gain vs. Collector Current (BC857B Type)

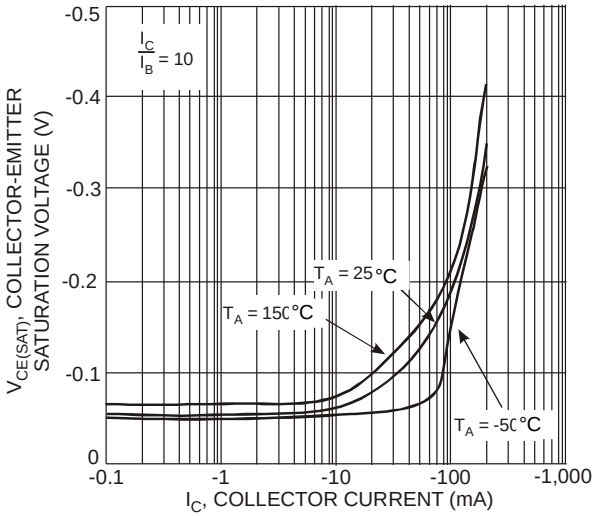


Figure 7. Typical Collector-Emitter Saturation Voltage vs. Collector Current (BC857B Type)

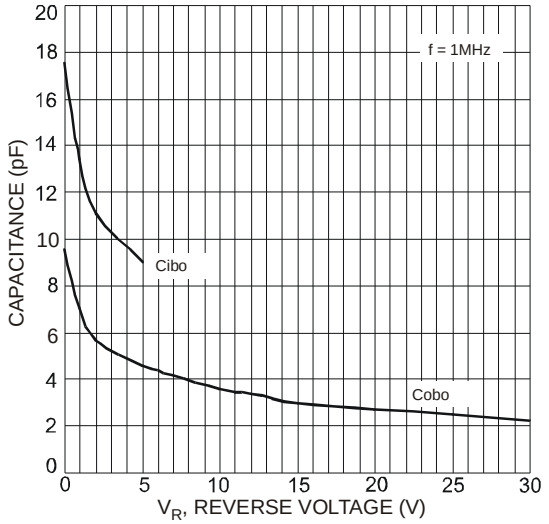


Figure 8. Typical Capacitance Characteristics (BC857B Type)

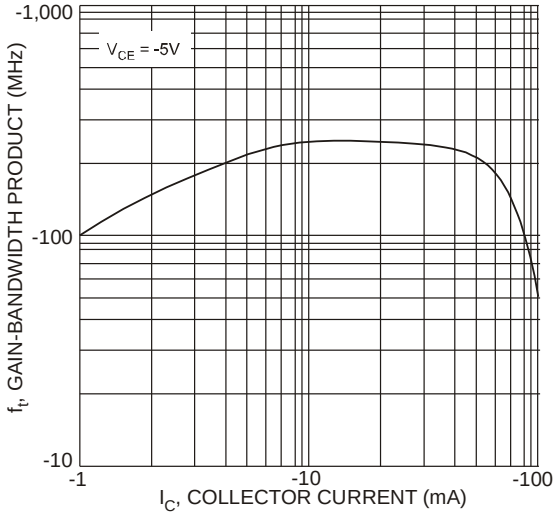


Figure 9. Typical Gain-Bandwidth Product vs. Collector Current (BC857B Type)

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

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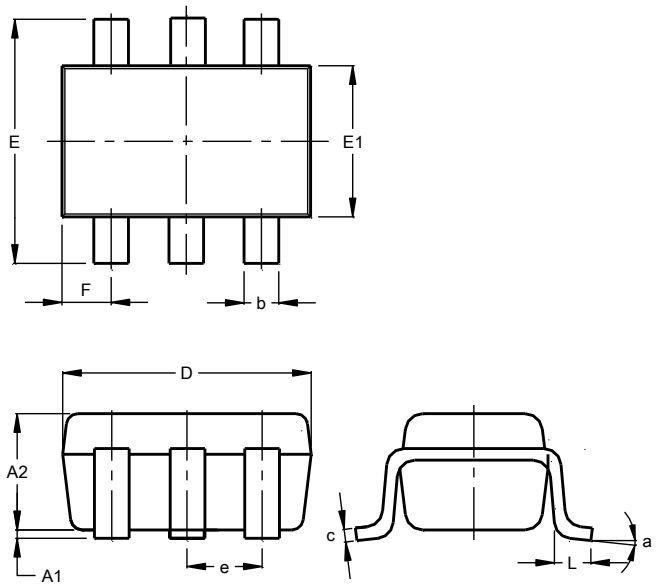

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Dim	**Min**	**Max**	**Typ**
A1	0.00	0.10	0.05
A2	0.90	1.00	1.00
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

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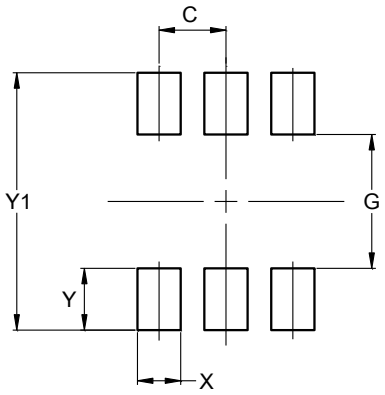

Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500

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